

IN THE CLAIMS

Please amend the claims as follows:

1. (Previously Presented) A memory array, comprising:
 - a number of memory cells having a first source/drain region and a second source/drain region and a gate region;
 - a number of source lines coupled to the first source/drain region of at least one memory cell;
 - a number of bit lines coupled to the second source/drain region of at least one memory cell;
 - a number of wordlines coupled to the gate region of at least one memory cell;
 - a strapping line of lower resistance than the wordlines coupled to a single continuous wordline in a single array, wherein the strapping line bypasses only a portion in a middle region between a first and second end of the single continuous wordline, wherein the strapping line is spaced apart from adjacent conductive structures by a distance greater than a wordline pitch, and wherein the strapping line bypasses only a portion of a wordline within the single memory array and bypasses a different portion of a wordline within the single array than an adjacent strapping line; and
 - at least two channels connecting the strapping line to a first and second end of the portion of the single continuous wordline.
2. (Original) The memory array of claim 1 wherein the strapping line comprises metal.
3. (Original) The memory array of claim 2 wherein the metal comprises a refractory metal.
4. (Original) The memory array of claim 1 wherein the portion of the wordline bypassed by the strapping line comprises a first half of the memory cells coupled to the wordline.

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5. (Previously Presented) A memory array, comprising:
- a number of memory cells having a first source/drain region and a second source/drain region and a gate region;
 - a number of source lines coupled to the first source/drain region of at least one memory cell;
 - a number of bit lines coupled to the second source/drain region of at least one memory cell;
 - a number of wordlines coupled to the gate region of at least one memory cell;
 - a plurality of separate strapping lines of lower resistance than the wordlines coupled to at least one of the number of wordlines in a single array wherein the strapping lines bypass a plurality of separate portions of a single continuous wordline, and wherein adjacent strapping lines bypass only a portion of a wordline within the memory array and bypass different portions of adjacent wordlines within the memory array; and
 - a plurality of channels connecting the plurality of strapping layers to the wordline.
6. (Original) The memory array of claim 5 wherein the plurality of strapping lines comprise metal.
7. (Original) The memory array of claim 6 wherein the metal comprises a refractory metal.
8. (Previously Presented) A memory device, comprising:
- a number of memory cells having a first source/drain region and a second source/drain region and a gate region, the memory cells forming a memory cell array;
 - a number of source lines coupled to the first source/drain region of at least one memory cell;
 - a number of bit lines coupled to the second source/drain region of at least one memory cell;
 - a single array of parallel wordlines coupled to the gate region of at least one memory cell, the array of parallel wordlines having a pitch;

a number of strapping devices which bypass portions of the wordlines in the single array of parallel wordlines, wherein at least one portion of a single continuous wordline is only in a middle region between a first and second end of the single continuous wordline, and wherein adjacent strapping devices bypass only a portion of a wordline within the memory array and bypass different portions of adjacent wordlines within the memory array, each strapping device comprising:

a strapping line of lower resistance than the wordlines, wherein the strapping lines are each located a distance from each other that is greater than the pitch; and

at least two channels connecting each strapping line to a portion of a single wordline.

9. (Original) The memory device of claim 8 wherein the strapping line comprises metal.

10. (Original) The memory device of claim 9 wherein the metal comprises a refractory metal.

11. (Original) The memory device of claim 8 wherein the portions of the wordlines in the array bypassed by the number of strapping devices comprises a plurality of end portions of the wordlines.

12. (Original) The memory device of claim 8 wherein the strapping devices are located on alternating wordlines in the array.

13. (Original) The memory device of claim 8 wherein the strapping devices are located on adjacent wordlines and staggered along the wordlines such that the portions of the adjacent wordlines that are bypassed are not adjacent to each other.

14. (Original) The memory device of claim 8 wherein the strapping devices strap a first half portion of a number of even wordlines in the array and a second half portion of a number of odd wordlines.

15. (Previously Presented) An integrated circuit comprising:
at least one memory array comprising:
a number of memory cells having a first source/drain region and a second source/drain region and a gate region;
a number of source lines coupled to the first source/drain region of at least one memory cell;
a number of bit lines coupled to the second source/drain region of at least one memory cell;
a number of wordlines in a single array coupled to the gate region of at least one memory cell;
a strapping line of lower resistance than the wordlines coupled to a single continuous wordline wherein the strapping line bypasses only a portion of the wordline within the memory array in a middle region between a first and second end of the single continuous wordline, wherein the strapping line is spaced apart from adjacent conductive structures by a distance greater than a wordline pitch, and wherein the strapping line bypasses a different portion of a wordline within the memory array than an adjacent strapping line;
at least two channels connecting the strapping line to a first and second end of the portion of the single continuous wordline;
a row decoder;
a column decoder; and
a sense amplifier.
16. (Original) The integrated circuit of claim 15 wherein the strapping line comprises metal.
17. (Original) The integrated circuit of claim 16 wherein the metal comprises a refractory metal.
18. (Original) The integrated circuit of claim 15 wherein the portion of the wordline bypassed by the strapping line comprises a first half of the memory cells coupled to the wordline.

19. (Previously Presented) An integrated circuit comprising:
- at least one memory array comprising:
 - a number of memory cells having a first source/drain region and a second source/drain region and a gate region;
 - a number of source lines coupled to the first source/drain region of at least one memory cell;
 - a number of bit lines coupled to the second source/drain region of at least one memory cell;
 - a single array of parallel wordlines coupled to the gate region of at least one memory cell, the array of parallel wordlines having a pitch;
 - a number of separate strapping devices which bypass separate portions of a single continuous wordline in the single array of parallel wordlines, and wherein adjacent strapping devices bypass only a portion of a wordline within the memory array and bypass different portions of adjacent wordlines within the single array, each strapping device comprising:
 - a strapping line of lower resistance than the wordlines, wherein the strapping lines are each located a distance from each other that is greater than the pitch;
 - at least two channels connecting the strapping line to the single continuous wordline;
 - a row decoder;
 - a column decoder; and
 - a sense amplifier.
20. (Original) The integrated circuit of claim 19 wherein the strapping line comprises metal.
21. (Original) The integrated circuit of claim 20 wherein the metal comprises a refractory metal.
22. (Original) The integrated circuit of claim 19 wherein the portions of the wordlines in the array bypassed by the number of strapping devices comprises a plurality of end portions of the wordlines.

23. (Original) The integrated circuit of claim 19 wherein the strapping devices are located on alternating wordlines in the array.

24. (Original) The integrated circuit of claim 19 wherein the strapping devices are located on adjacent wordlines and staggered along the wordlines such that the portions of the adjacent wordlines that are bypassed are not adjacent to each other.

25. (Original) The integrated circuit of claim 19 wherein the strapping devices strap a first half portion of a number of even wordlines in the array and a second half portion of a number of odd wordlines.

26. (Previously Presented) An information handling device comprising:

a processing unit;

at least one memory array comprising:

a number of memory cells having a first source/drain region and a second source/drain region and a gate region;

a number of source lines coupled to the first source/drain region of at least one memory cell;

a number of bit lines coupled to the second source/drain region of at least one memory cell;

a number of wordlines in a single array coupled to the gate region of at least one memory cell;

a strapping line of lower resistance than the wordlines coupled to a single continuous wordline wherein the strapping line bypasses only a portion in a middle region between a first and second end of the single continuous wordline and bypasses only a portion of the wordline within the memory array, wherein the strapping line is spaced apart from adjacent conductive structures by a distance greater than a wordline pitch, and wherein the strapping line bypasses a different portion of a wordline within the memory array than an adjacent strapping line;

at least two channels connecting the strapping line to the single continuous wordline; and

a system bus connecting the processing unit to the memory array.

27. (Original) The information handling device of claim 26 wherein the strapping line comprises metal.

28. (Original) The information handling device of claim 27 wherein the metal comprises a refractory metal.

29. (Original) The information handling device of claim 26 wherein the portion of the wordline bypassed by the strapping line comprises a first half of the memory cells coupled to the wordline.

30. (Previously Presented) An information handling device comprising:
a processing unit;
at least one memory array comprising:

a number of memory cells having a first source/drain region and a second source/drain region and a gate region;

a number of source lines coupled to the first source/drain region of at least one memory cell;

a number of bit lines coupled to the second source/drain region of at least one memory cell;

a single array of parallel wordlines coupled to the gate region of at least one memory cell, the array of parallel wordlines having a pitch;

a number of strapping devices which bypass only portions of the wordlines in the single array of parallel wordlines, wherein at least one portion of a single continuous wordline is in a middle region between a first and second end of the single continuous wordline, and wherein adjacent strapping devices bypass only a portion of the wordline within the memory array and

bypass different portions of adjacent wordlines within the memory array, each strapping device comprising:

a strapping line of lower resistance than the wordlines, wherein the strapping lines are each located a distance from each other that is greater than the pitch; and
at least two channels connecting each strapping line to single wordlines;

and

a system bus connecting the processing unit to the memory array.

31. (Original) The information handling device of claim 30 wherein the strapping line comprises metal.

32. (Original) The information handling device of claim 31 wherein the metal comprises a refractory metal.

33. (Original) The information handling device of claim 30 wherein the portions of the wordlines in the array bypassed by the number of strapping devices comprises a plurality of end portions of the wordlines.

34. (Original) The information handling device of claim 30 wherein the strapping devices are located on alternating wordlines in the array.

35. (Original) The information handling device of claim 30 wherein the strapping devices are located on adjacent wordlines and staggered along the wordlines such that the portions of the adjacent wordlines that are bypassed are not adjacent to each other.

36. (Original) The information handling device of claim 30 wherein the strapping devices strap a first half portion of a number of even wordlines in the array and a second half portion of a number of odd wordlines.

37. (Previously Presented) A method of reducing a wordline RC time constant comprising:
spacing a number of strapping devices over wordlines within a single memory array apart from adjacent strapping devices by a distance greater than a wordline pitch, wherein adjacent strapping devices bypass different portions of adjacent wordlines within the single memory array;

connecting individual strapping devices to portions in a middle region between a first and second end of single continuous wordlines using at least two channels for each strapping device;
activating a first number of transistors coupled to a first portion of a wordline; and
activating a second number of transistors coupled to a second portion of a wordline,
wherein a signal used for activating the second number of transistors bypasses the first portion of the wordline through a strapping device of lower resistance than the first portion of the wordline;
activating a selected bitline in the memory array associated with a selected memory cell;
discharging the selected memory cell through a selected transistor, the selected transistor being activated by both the selected row and the selected bitline; and
sensing the presence or absence of a charge from the selected memory cell through the use of a sense amplifier.

38. (Original) The method of reducing a wordline RC time constant of claim 37, wherein activating a second number of transistors coupled to a second portion of a wordline comprises:
sending a signal through a first channel to a metal strapping line;
sending the signal through the metal strapping line; and
sending the signal through a second channel to the second portion of the wordline.

39. (Original) The method of reducing a wordline RC time constant of claim 38, wherein sending the signal through the metal strapping line comprises sending the signal through a refractory metal strapping line.

40. (Original) The method of reducing a wordline RC time constant of claim 37, wherein activating a first number of transistors coupled to a first portion of a wordline comprises activating a first number of transistors coupled to a first half of the wordline.

41. (Original) The method of reducing a wordline RC time constant of claim 37, wherein activating a selected row in a memory array comprises bypassing multiple portions of the wordline using multiple strapping devices of lower resistance than the wordline.

42-44. (Canceled)

45. (Previously Presented) A method of forming a memory device comprising:
forming a number of memory cells having a first source/drain region and a second source/drain region and a gate region, the memory cells forming a memory cell array;
coupling a number of source lines to the first source/drain region of at least one memory cell;

coupling a number of bit lines to the second source/drain region of at least one memory cell;

attaching a number of wordlines to the gate region of at least one memory cell to form a single array;

attaching a strapping line of lower resistance than the wordlines to a single continuous wordline wherein the strapping line bypasses only a portion in a middle region between a first and second end of the single continuous wordline, wherein the strapping line is spaced apart from adjacent conductive structures by a spacing greater than a wordline pitch and wherein the strapping line bypasses only a portion of a wordline within the memory cell array and bypasses a different portion of a wordline within the memory cell array than an adjacent strapping line; and

connecting the strapping line to the single wordline by forming at least two channels from the strapping line to the single continuous wordline.

46. (Original) The method of forming a memory device of claim 45, wherein attaching at least one strapping line of lower resistance than the wordlines to at least one of the number of wordlines comprises attaching at least one metal strapping line.

47. (Original) The method of forming a memory device of claim 46, wherein attaching at least one metal strapping line comprises attaching at least one refractory metal strapping line.

48. (Original) The method of forming a memory device of claim 45, wherein attaching at least one strapping line of lower resistance than the wordlines to at least one of the number of wordlines comprises attaching multiple strapping lines to bypass multiple portions of a single wordline.

49. (Previously Presented) A method of forming a memory device comprising:
forming a number of memory cells having a first source/drain region and a second source/drain region and a gate region, the memory cells forming a memory cell array;
coupling a number of source lines coupled to the first source/drain region of at least one memory cell;

coupling a number of bit lines coupled to the second source/drain region of at least one memory cell;

attaching a single array of parallel wordlines to the gate region of at least one memory cell, the single array of parallel wordlines having a pitch;

attaching a number of strapping lines of lower resistance than the wordlines which bypass portions of the wordlines in the array of parallel wordlines and bypass only a portion of a wordline within the memory cell array and, wherein at least one portion of a single continuous wordline is only in a middle region between a first and second end of the single continuous wordline, wherein the strapping lines are each located a distance from each other that is greater than the pitch, and wherein adjacent strapping lines bypass different portions of adjacent wordlines within the memory cell array; and

connecting the strapping lines to the wordlines by forming at least two channels from each strapping line to individual wordlines.

50. (Original) The method of forming a memory device of claim 49, wherein attaching a number of strapping lines comprises attaching a number of metal strapping lines.

51. (Original) The method of forming a memory device of claim 50, wherein attaching a number of metal strapping lines comprises attaching a number of refractory metal strapping lines.

52. (Original) The method of forming a memory device of claim 49, wherein attaching a number of strapping lines comprises attaching the strapping lines on alternating wordlines in the array.

53. (Original) The method of forming a memory device of claim 49, wherein attaching the strapping lines comprises attaching the strapping lines on adjacent wordlines and staggering the strapping lines along the wordlines such that the portions of the adjacent wordlines that are bypassed are not adjacent to each other.

54. (Original) The method of forming a memory device of claim 49, wherein attaching a number of strapping lines comprises attaching the strapping lines on a first half portion of a number of even wordlines in the array and attaching the strapping lines on a second half portion of a number of odd wordlines.

55. (New) A memory device comprising:

- a memory array including a number of memory cells;
- an even row decoder located on a first side of the memory array;
- an odd row decoder located on a second side of the memory array;
- a single column decoder connected to the memory array;
- a number of parallel wordlines local to the memory array coupled to gate regions of memory cells, including one or more even wordlines coupled to the even row decoder, and one or more odd wordlines coupled to the odd row decoder, the odd wordlines arranged alternately with the even wordlines; and
- a number of strapping lines having lower resistance than the wordlines and connected to bypass portions of the wordlines within the memory array, wherein a strapping line connected to an odd wordline bypasses only a portion of the odd wordline within the memory array nearer the odd row decoder, wherein a strapping line connected to an even wordline bypasses only a portion of the even wordline within the memory array nearer the even row decoder.

56. (New) The memory device of claim 55, wherein the even row decoder is located directly adjacent the first side and the odd row decoder is located directly adjacent the second side.

57. (New) The memory device of claim 55, wherein a strapping line connected to an odd wordline bypasses only one half of the wordline within the memory array nearer the odd row decoder and a strapping line connected to an even wordline bypasses only one half of the wordline within the memory array nearer the even row decoder.